

RD5CYDT08

IGBT Driver / CMOS Logic Level Shifter

REJ03D0181-0400Z Rev.4.00 Jul. 12, 2004

Description

The RD5CYDT08 has two-input AND gate in a 5 pin package. This product is suited as IGBT Driver IC for the strobe.

Features

- Supplied on emboss taping for high-speed automatic mounting.
- TTL compatible input level

Supply voltage range: 4.0 to 6.0 V

Operating temperature range: -40 to +85°C

- Logic-level translate function 3.0 V CMOS logic → 5.0 V CMOS logic
- · High drive current

$$I_{OH}$$
 short = -130 mA (min) (@V_{CC} = 5.0 V)

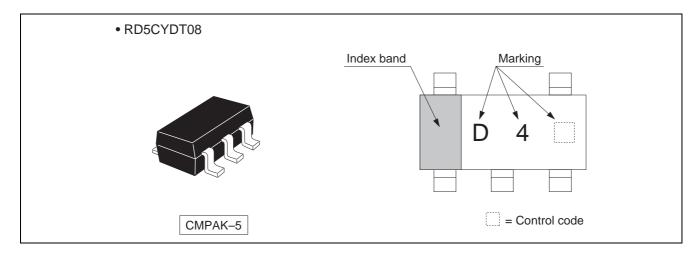
• Low sink current

$$I_{OL}$$
 short = 40 mA (max) (@V_{CC} = 5.0 V)

• Ordering Information

			Package	Taping Abbreviation
Part Name	Package Type	Package Code	Abbreviation	(Quantity)
RD5CYDT08CME	CMPAK-5 pin	CMPAK-5V	СМ	E (3,000 pcs/reel)
		CMPAK-5V(O)		

Outline and Article Indication

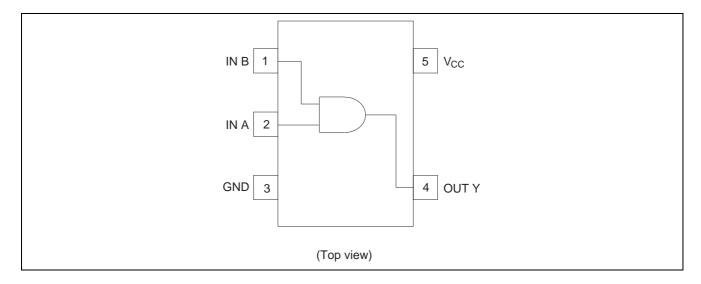


Function Table

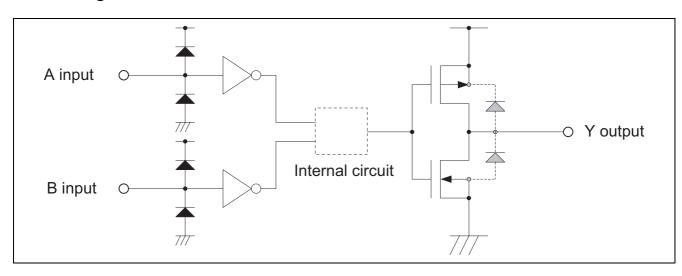
Inp		
Α	В	Output Y
L	L	L
Н	L	L
L	Н	L
Н	Н	Н

H : High level L : Low level

Pin Arrangement



Block Diagram



Absolute Maximum Ratings

Item	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V _{CC}	-0.5 to 7.0	V	
Input voltage range *1	Vı	-0.5 to V _{CC} + 0.5	V	
Output voltage range *1, 2	Vo	-0.5 to V _{CC} + 0.5	V	
Input clamp current	I _{IK}	±20	mA	$V_I < 0$ or $V_I > V_{CC}$
Output clamp current	I _{OK}	±50	mA	$V_O < 0$ or $V_O > V_{CC}$
Continuous output current	Io	-200	mA	V _O = 0
		100		$V_O = V_{CC}$
Continuous current through	I _{CC} or I _{GND}	±200	mA	
V _{CC} or GND				
Maximum power dissipation	P _T	200	mW	
at Ta = 25°C (in still air) *3				
Storage temperature	Tstg	-65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore no two of which may be realized at the same time.

- 1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed. When Over shoot / Under shoot pulse width is under 10 ns, input and output voltage permit to -15 V or V_{CC}+1.5 V.
- 2. This value is limited to 5.5 V maximum.
- 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V _{CC}	4.0	6.0	V	
Input voltage range	VI	0	Vcc	V	
Output voltage range	Vo	0	V _{CC}	V	
Operating free-air temperature	Ta	-40	85	°C	

Note: Unused or floating inputs must be held high or low.

Electrical Characteristic

 $Ta = -40 \text{ to } 85^{\circ}\text{C}$

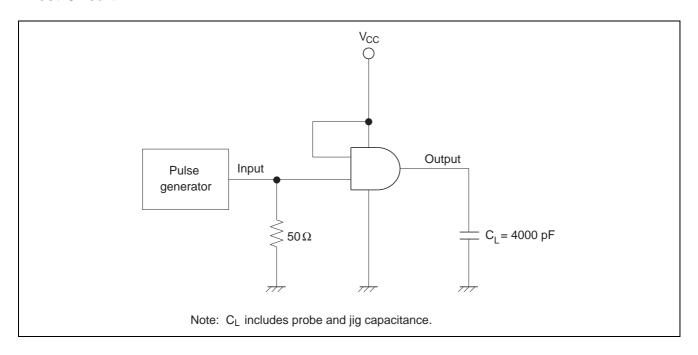
Item	Symbol	V _{cc} (V)	Min	Тур	Max	Unit	Test condition
Input voltage	V_{IH}	4.5 to 5.5	2.0	_	_	V	
	V _{IL}	4.5 to 5.5	_	_	0.8		
Output current	I _{OH} short	5.0	-100	-130	-160	mA	$V_O = 0 V$
	I _{OL} short	5.0	30	40	50		$V_O = V_{CC}$
Input current	I _{IN}	5.5	_	_	±5	μΑ	$V_{IN} = 5.5 \text{ V or GND}$
Quiescent	I _{CC}	5.5	_	_	10	μΑ	$V_{IN} = V_{CC}$ or GND,
supply current							$I_{O} = 0$
Input capacitance	C _{IN}	5.0	_	2.5		pF	$V_{IN} = V_{CC}$ or GND

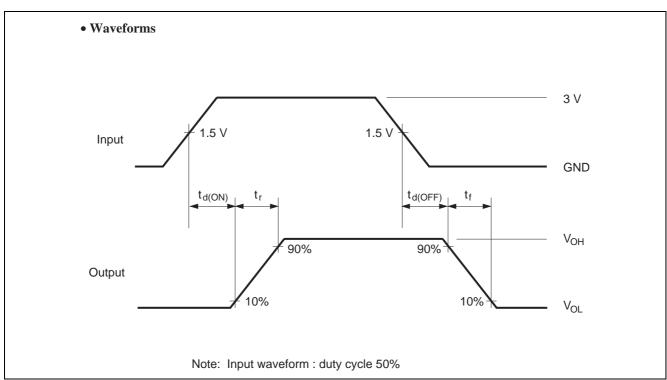
Switching Characteristics

 $V_{CC}=5.0\pm0.5~V$

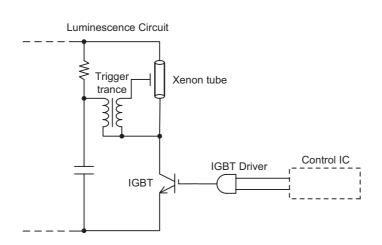
		Ta:	= -40 to 8	35°C		Test	FROM	ТО
Item	Symbol	Min	Тур	Max	Unit	Conditions	(Input)	(Output)
Propagation delay time	t _{d(ON)}	_	_	70	ns	C _L = 4000 pF	A or B	Υ
	$t_{d(OFF)}$	_	_	140				
Output rise time	t _r	_	_	800				
Output fall time	t _f	_	_	1500				

Test Circuit





Application Example (Strobe circuit)



Combination example

SYSTEM	IGBT	IGBT Driver	Control IC
5.0 V	CY25BAJ –8F CY25AAJ –8F	RD5CYD08 ← RD5CYDT08 ←	5.0 V signal 3.3 V signal
3.3 V	CY25BAH–8F ◀	RD3CYD08	3.3 V signal

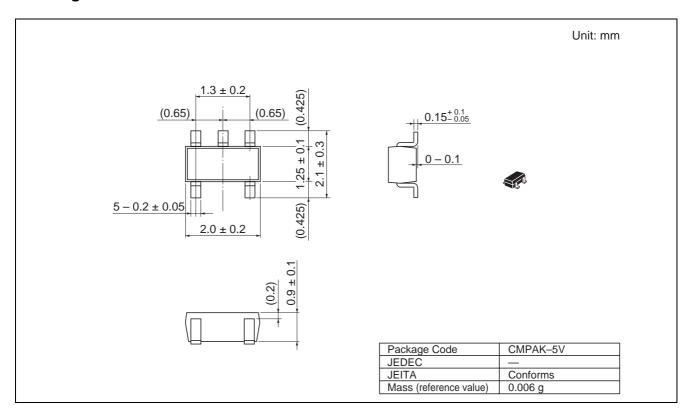
IGBT Driver Lineup

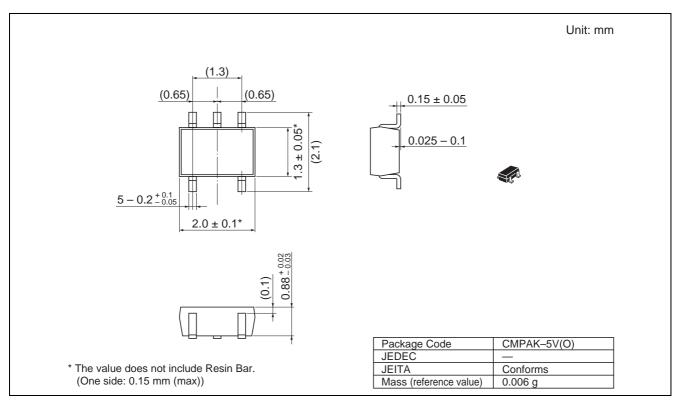
TYPE No.	Specification	Package
RD5CYDT08	Vcc = 4.0 to 6.0V TTL level input I _{OH} (short) = -130mA(typ) @ Vcc=5.0V I _{OL} (short) = 40mA(typ) @ Vcc=5.0V	
RD5CYD08	Vcc = 4.0 to 6.0V CMOS level input I _{OH} (short) = -130mA(typ) @ Vcc=5.0V I _{OL} (short) = 40mA(typ) @ Vcc=5.0V	CMPAK-5
RD3CYD08	$Vcc = 2.0 \text{ to } 3.6 \text{V CMOS level input}$ $I_{OH}(\text{short}) = -130 \text{mA(typ)} \text{ @ Vcc=} 3.3 \text{V}$ $I_{OL}(\text{short}) = 45 \text{mA(typ)} \text{ @ Vcc=} 3.3 \text{V}$	

IGBT Lineup

TYPE No.	Specification	Package
CY25AAJ-8F	$V_{CES} = 400V(max)$, $I_{CP} = 150A(max)$, 4V drive	TSSOP-8
CY25BAJ-8F	V _{CES} = 400V(max), I _{CP} = 150A(max), 4V drive	10001-0
CY25BAH-8F	$V_{CES} = 400V(max), I_{CP} = 150A(max), 2.5V drive$	SOP-8

Package Dimensions





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